

and a laser light.

sub F1 47. (Amended) A method according to claim 45, wherein said semiconductor flim is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

48. (Amended) A method according to claim 45, wherein said gate insulating film is continuously formed without exposing to the air after forming said semiconductor film.

SUB E2
D1
cont 49. (Amended) A method for manufacturing a semiconductor device comprising steps of:
contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
subjecting said semiconductor film to plasma comprising oxygen and helium; and
irradiating said semiconductor film subjected to the plasma with one of an infrared ray and a laser light.

50. (Amended) A method according to claim 49, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

SUB E3
D2 52. (Amended) 322A method for manufacturing a semiconductor device comprising steps of:
contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
subjecting said semiconductor film to oxygen plasma; and
crystallizing said semiconductor film subjected to the oxygen plasma using said material, to obtain a crystalline semiconductor film.

53. (Amended) A method according to claim 52, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.

D2
cont

54. (Amended) A method according to claim 52, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

SUB E4 >

D3

56. (Amended) A method for manufacturing a semiconductor device comprising steps of:

- contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;
- subjecting said semiconductor film to oxygen plasma;
- irradiating said semiconductor film subjected to the oxygen plasma with one of an infrared ray and a laser light; and
- patterning said crystalline semiconductor film.

D4

58. (Amended) A method according to claim 56, wherein said semiconductor film is crystallized through one of a solid state and an intermediate state between the solid state and a liquid state.

SUB E5 >

D5

60. (Amended) A method for manufacturing a semiconductor device comprising steps of:

- contacting at least one metal element to at least a part of a semiconductor film formed over a substrate;
- subjecting said semiconductor film to plasma;
- crystallizing said semiconductor film subjected to the oxygen plasma to obtain a crystalline semiconductor film; and
- patterning said crystalline semiconductor film.

61. (Amended) A method according to claim 60, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with one of an infrared ray and a laser light.